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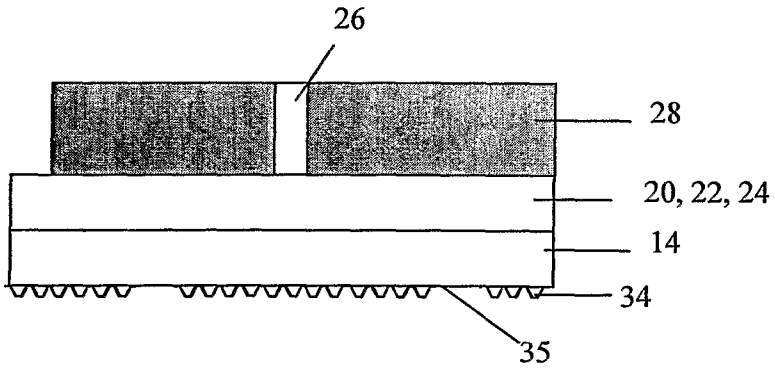
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(54) Title: FABRICATION OF SEMICONDUCTOR DEVICES



(57) Abstract: A method for fabrication of a semiconductor device, the semiconductor device having a plurality of epitaxial layers on a substrate. The plurality of epitaxial layers include an active region in which light is able to be generated. The method comprises applying at least one first ohmic contact layer to a front surface of the epitaxial layer, the first ohmic contact layer also acting as a reflector. The substrate is then removed from a rear surface of the epitaxial layers. The rear surface is then textured.

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